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TO-252 N MOS

N-Channel Enhancement Mode Field Effect Transistor in a TO-252 Plastic Package.

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V_{DS} (V) = 30V I_D =122 A (V_{GS} = 20V)

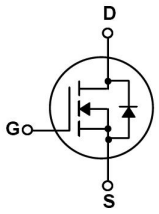
$R_{DS(ON)}$@10V 3.5mR(Typ.3.4mR)

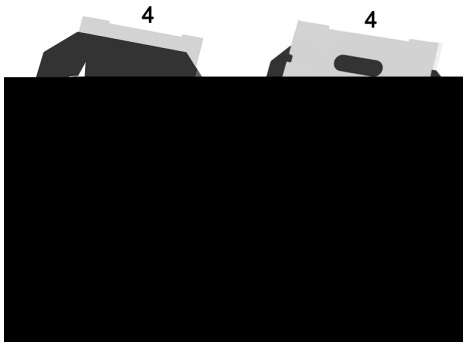
$R_{DS(ON)}$@4.5V 6.5mR(Typ.5.0mR)

AEC-Q101 Qualified to AEC-Q101 Standards for High Reliability, HF Product.

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Load Switch Applications,Battery Power Management, Meet the stringent requirements of automotive applications.





PIN1 G PIN 2 4 D PIN 3 S

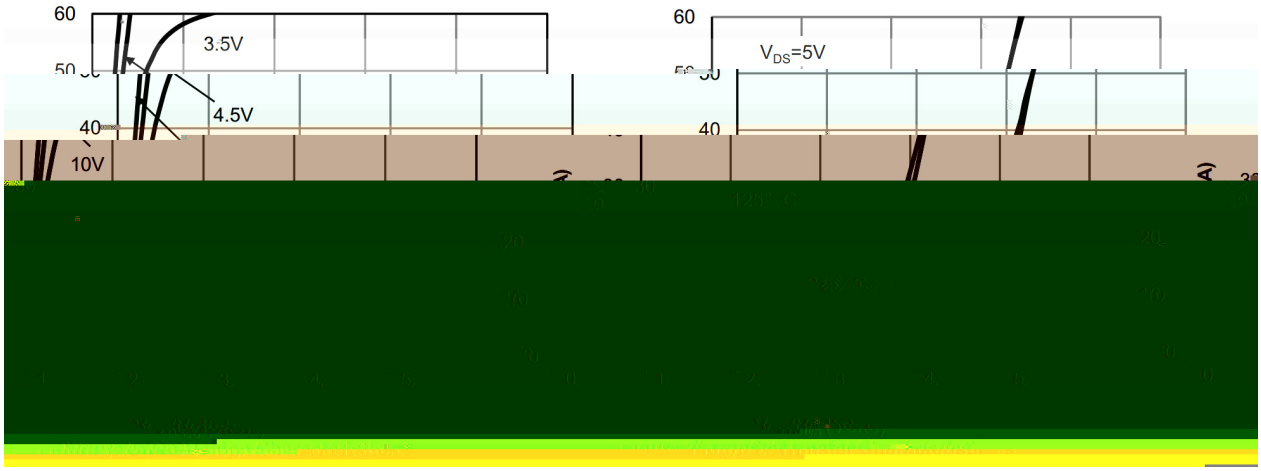
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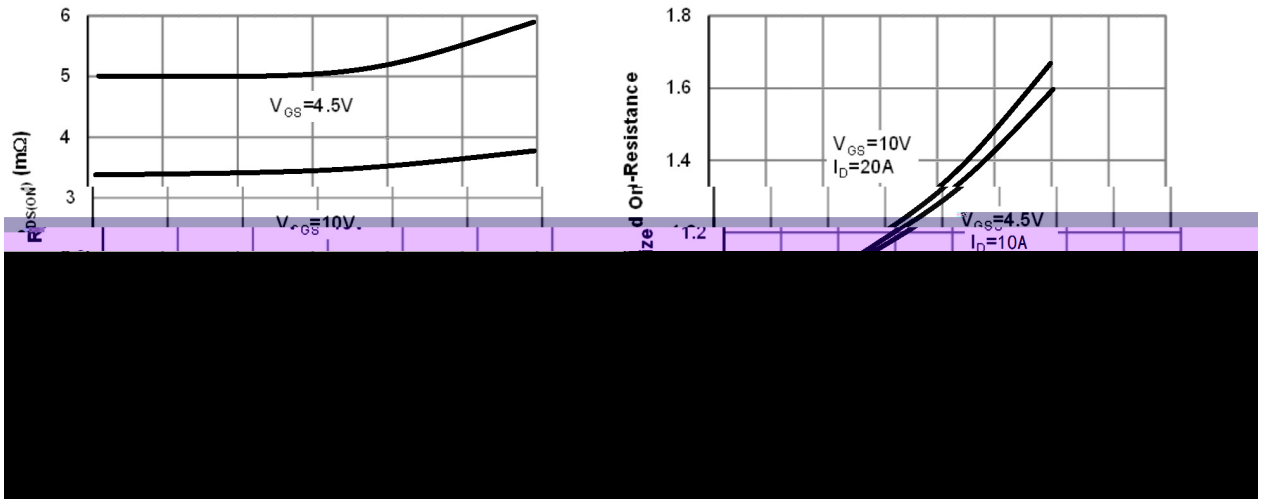
See Marking Instructions.

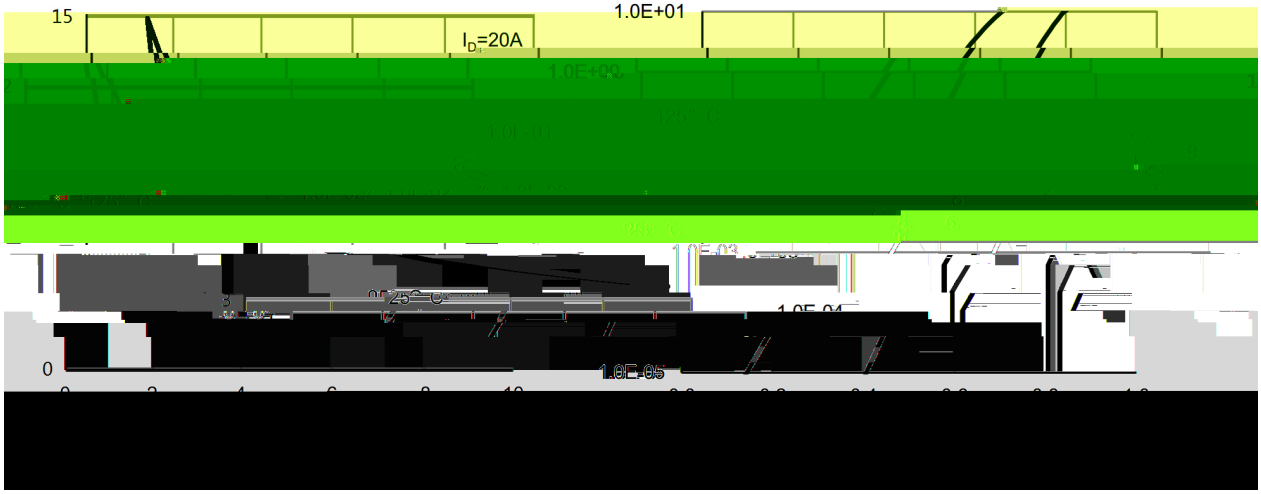
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	30	V
Drain Current	I_D(Tc=25)		

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	$Q_{g(10V)}$	V_{GS}=10V V_{DS}=15V I_D=20A		32		nC
Total Gate Charge	$Q_{g(4.5V)}$			15		
Gate Source Charge	Q_{gs}			5.2		
Gate Drain Charge	Q_{gd}			6.5		
Turn-On Delay Time	$t_{d(on)}$			8.5		ns
Turn-On Rise Time	t	V_{GS}=10V V_{DS}=15V R_L=0.75 R_{GEN}=3				

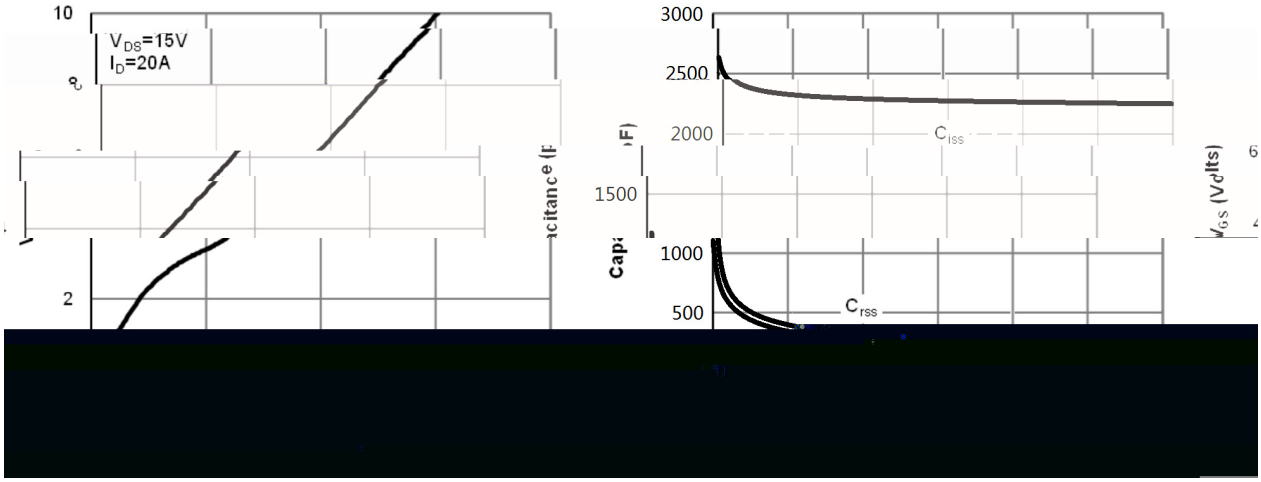
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60
50
40
3.5V
4.5V
10V
60
40
V_{DS}=5V


6
5
4
3
V_{GS}=4.5V
V_{GS}=10V
1.8
1.6
1.4
1.2
V_{GS}=10V
I_D=20A
V_{GS}=4.5V
I_D=10A


15
I_D=20A
1.0E+01
0
1.0E-05

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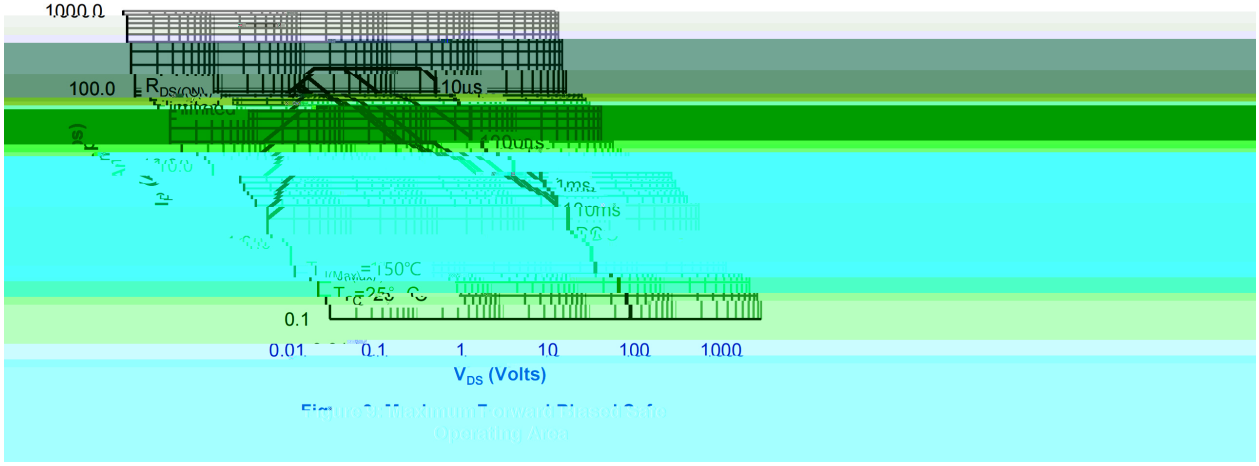


Figure 9: Maximum Forward Biased Safe Operating Area

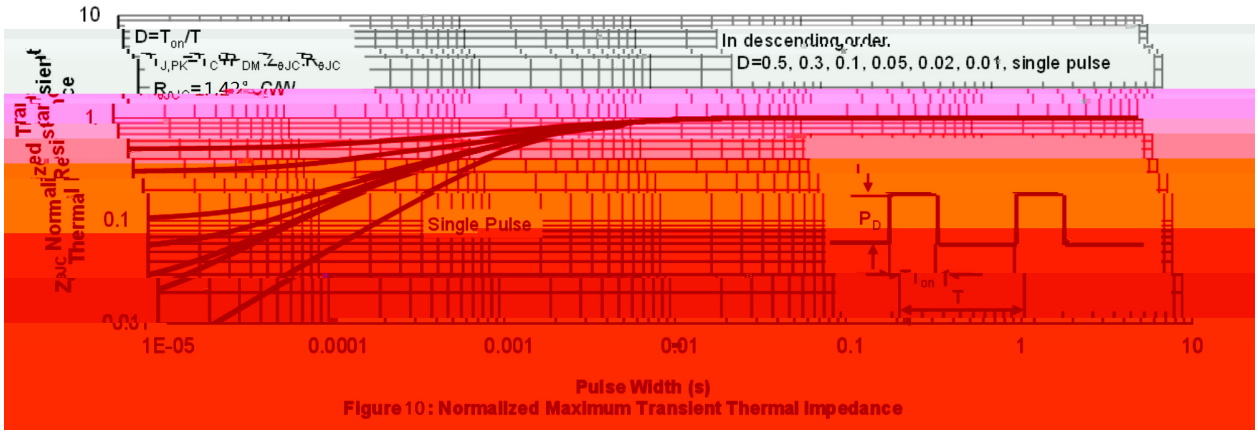
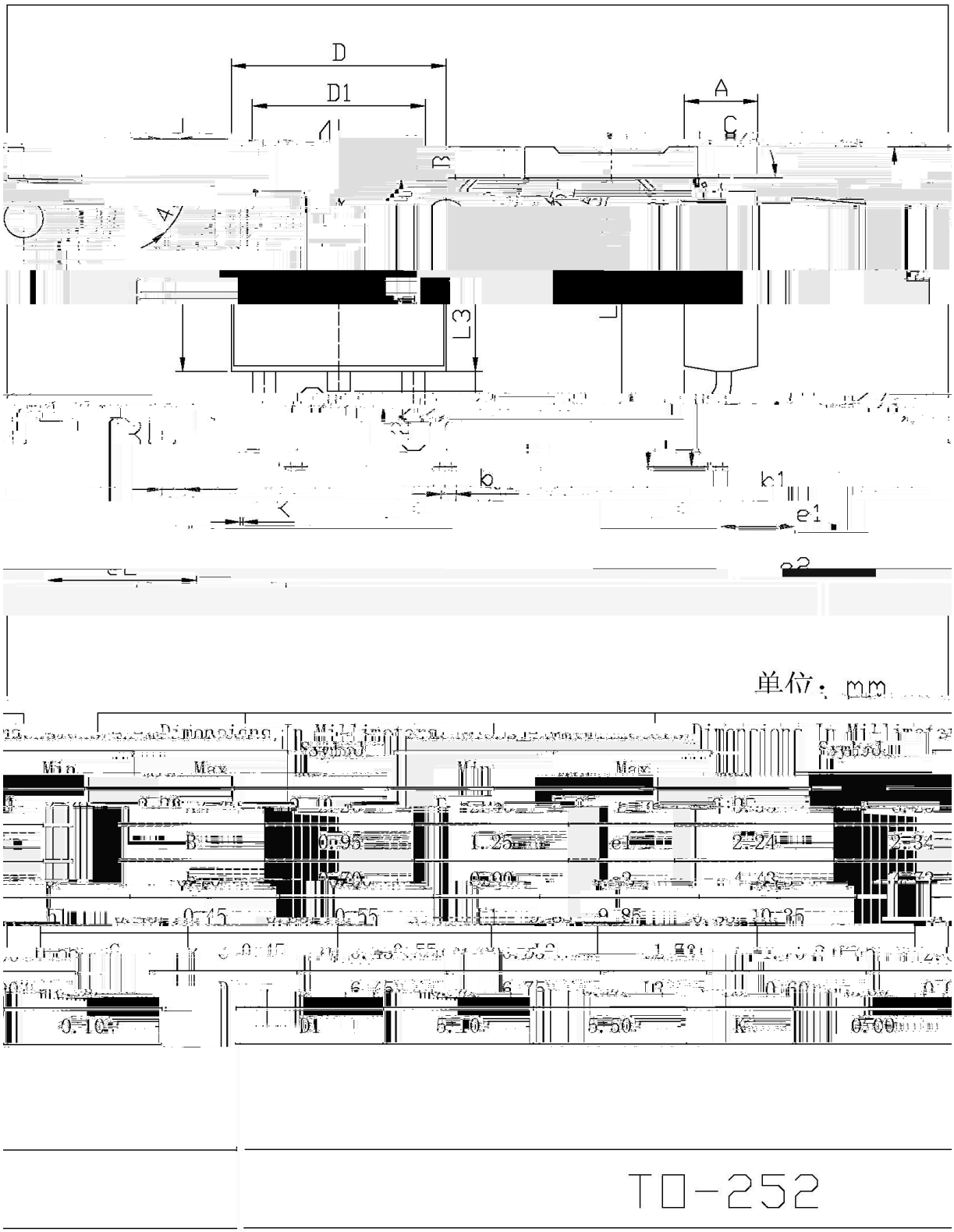
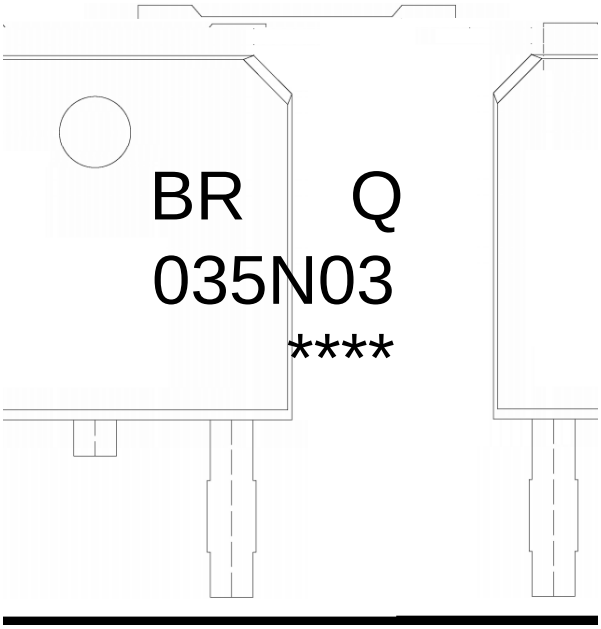


Figure 10: Normalized Maximum Transient Thermal Impedance

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D
D1
A
L3
b
k1
e1
e2
单位：mm
Dimensions In Millimeters
Symbol
Min
Max
TO-252

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BR

Q

035N03

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Note:

BR:	Company Code
Q:	Automobile halogen-free product Code
035N03:	Product Type Code
****:	Lot No. Code, code change with Lot No

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Note:

1		150	200		60	120sec;
2		255±5				5±0.5sec;
3				2	10	/sec.

1.Preheating:150~200 , Time:60~120sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.